NTR4518N

Power MOSFET

30 V, 2.5 A, Single N−Channel, SOT−23

Features

- Leading Planar Technology for Low Gate Charge / Fast Switching
- 4.5 V Rated for Low Voltage Gate Drive
- SOT−23 Surface Mount for Small Footprint (3 x 3 mm)
- This is a Pb−Free Device

Applications

- DC−DC Conversion
- Load/Power Switch for Portables
- Load/Power Switch for Computing

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	30	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current (Note 1)	Steady State	T_A = 25°C	I_D	2.0	A
		T_A = 85°C		1.5	
	t ≤ 10 s	T_A = 25°C		2.5	
Power Dissipation (Note 1)	Steady State	T_A = 25°C	P_D	0.73	W
Continuous Drain Current (Note 2)	Steady State	T_A = 25°C	I_D	1.5	A
		T_A = 85°C		1.1	
Power Dissipation (Note 2)		T_A = 25°C	P_D	0.42	W
Pulsed Drain Current	t_p = 10 μs		I_{DM}	6.0	A
ESD Capability (Note 3)	C = 100 pF, RS = 1500 Ω		ESD	125	V
Operating Junction and Storage Temperature			T_J, T_{stg}	−55 to 150	°C
Source Current (Body Diode)			I_S	2.0	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

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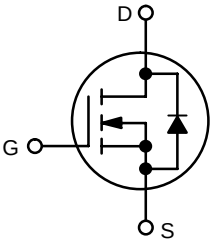
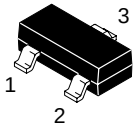
$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX
30 V	85 mΩ @ 10 V	2.5 A
	105 mΩ @ 4.5 V	

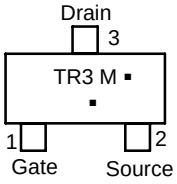
N−Channel





SOT−23
CASE 318
STYLE 21

MARKING DIAGRAM/ PIN ASSIGNMENT



TR3 = Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
NTR4518NT1G	SOT−23 (Pb−Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction−to−Ambient − Steady State (Note 1)	$R_{\theta JA}$	170	°C/W
Junction−to−Ambient − t < 10 s (Note 1)	$R_{\theta JA}$	100	
Junction−to−Ambient − Steady State (Note 2)	$R_{\theta JA}$	300	

1. Surface−mounted on FR4 board using 1 in sq pad size.
2. Surface−mounted on FR4 board using the minimum recommended pad size.
3. ESD Rating Information: HBM Class 0.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA	30	36		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 24 V			1.0	μA
		V_{GS} = 0 V, V_{DS} = 24 V, T_J = 125°C			10	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA	1.0	1.75	3.0	V
Drain−to−Source On−Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 2.5 A		85	110	mΩ
		V_{GS} = 4.5 V, I_D = 2.0 A		105	140	
Forward Transconductance	g_{FS}	V_{DS} = 4.5 V, I_D = 2.5 A		5.3		S
CHARGES AND CAPACITANCES						
Input Capacitance	C_{iss}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 15 V		135		pF
Output Capacitance	C_{oss}			52		
Reverse Transfer Capacitance	C_{rss}			15		
Input Capacitance	C_{iss}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 24 V		130	250	pF
Output Capacitance	C_{oss}			42	75	
Reverse Transfer Capacitance	C_{rss}			13	25	
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 15 V, I_D = 2.5 A		3.6	7.0	nC
Threshold Gate Charge	$Q_{G(TH)}$			0.3		
Gate−to−Source Charge	Q_{GS}			0.6		
Gate−to−Drain Charge	Q_{GD}			0.7		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 24 V, I_D = 2.5 A		1.9		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.3		
Gate−to−Source Charge	Q_{GS}			0.6		
Gate−to−Drain Charge	Q_{GD}			0.9		
SWITCHING CHARACTERISTICS (Note 5)						
Turn−On Delay Time	$t_{d(on)}$	V_{GS} = 10 V, V_{DD} = 15 V, I_D = 1 A, R_G = 6 Ω		5.8	12	ns
Rise Time	t_r			5.8	10	
Turn−Off Delay Time	$t_{d(off)}$			14	25	
Fall Time	t_f			1.6	5.0	
Turn−On Delay Time	$t_{d(on)}$	V_{GS} = 10 V, V_{DD} = 24 V, I_D = 2.5 A, R_G = 2.5 Ω		4.8		ns
Rise Time	t_r			6.7		
Turn−Off Delay Time	$t_{d(off)}$			13.6		
Fall Time	t_f			1.8		

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
DRAIN−SOURCE DIODE CHARACTERISTICS						
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 2.0 A		0.85	1.2	V
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, I_S = 2.0 A, dI_S/dt = 100 A/μs		9.2		ns
Reverse Recovery Charge	Q_{RR}			4.0		nC

4. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
5. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

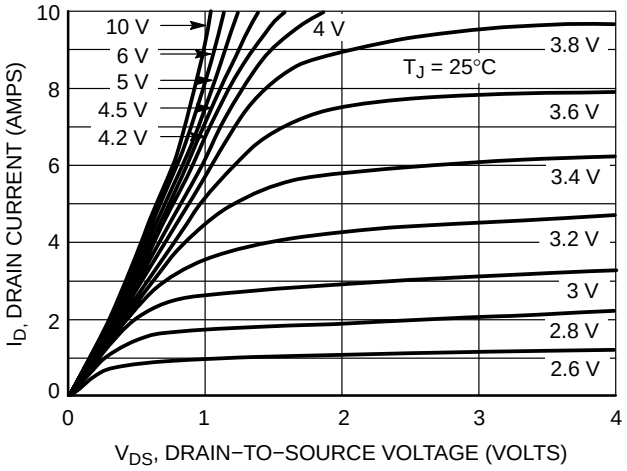


Figure 1. On−Region Characteristics

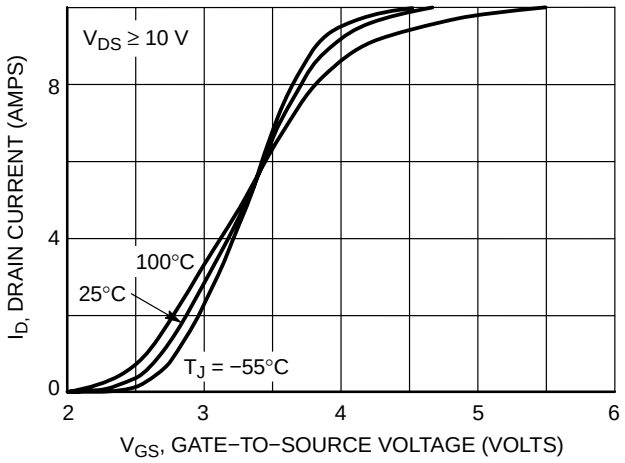


Figure 2. Transfer Characteristics

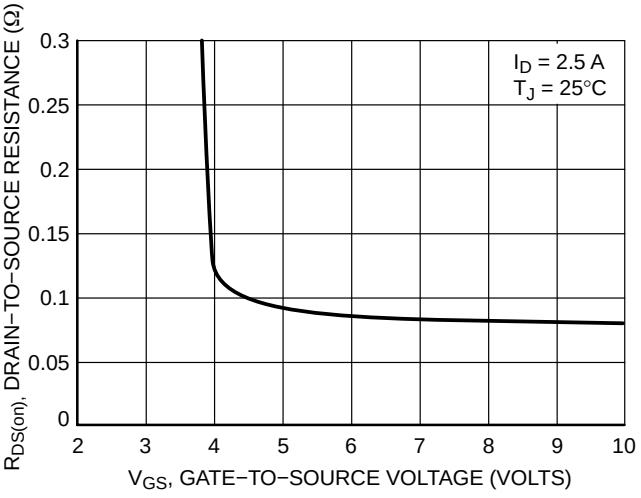


Figure 3. On−Resistance vs. Gate−to−Source Voltage

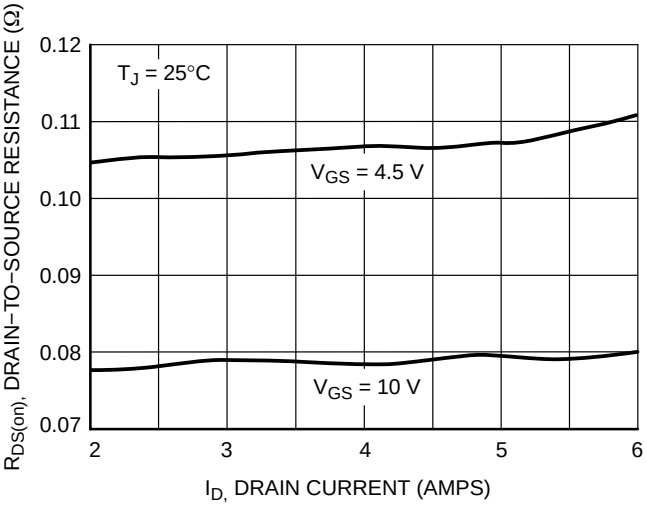


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

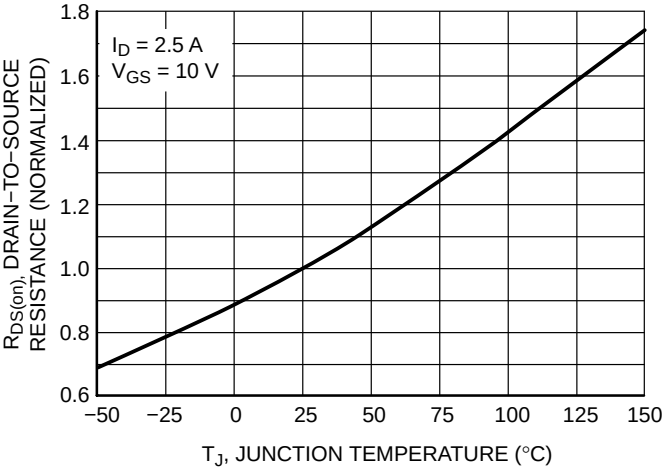


Figure 5. On−Resistance Variation with Temperature

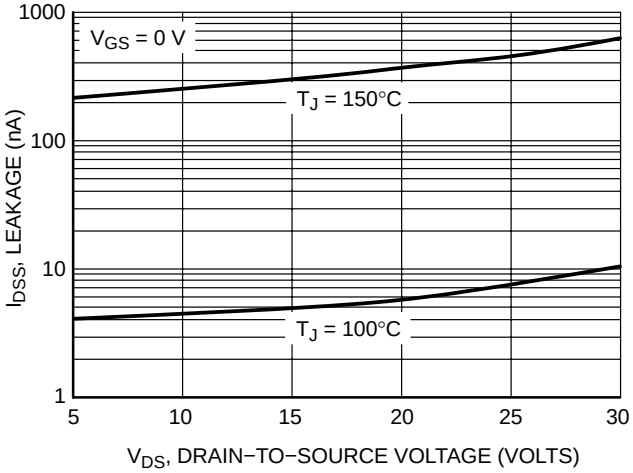


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES

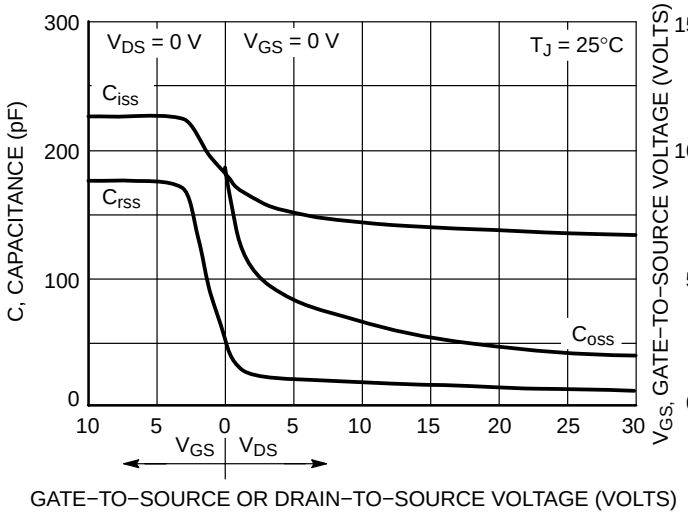


Figure 7. Capacitance Variation

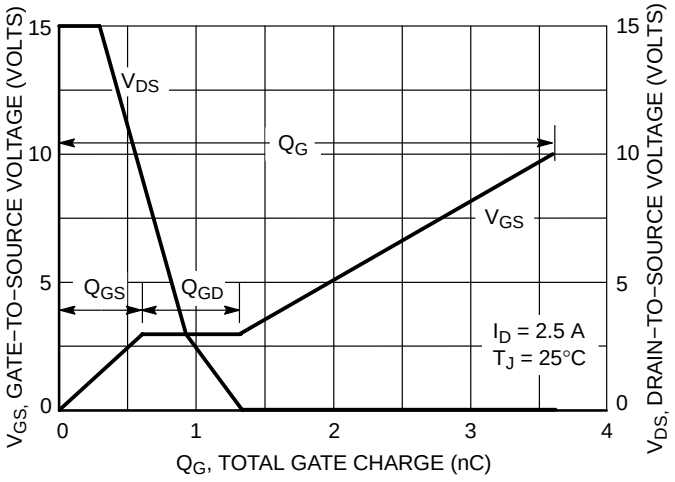


Figure 8. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

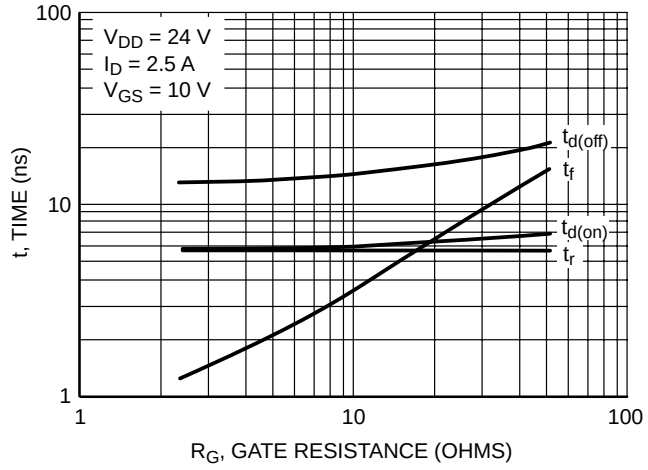


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

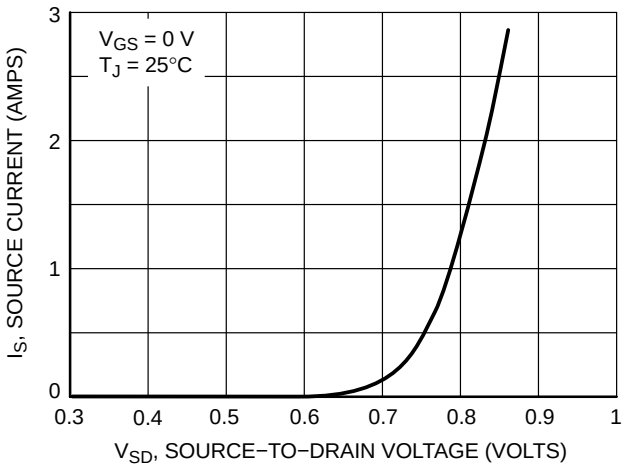
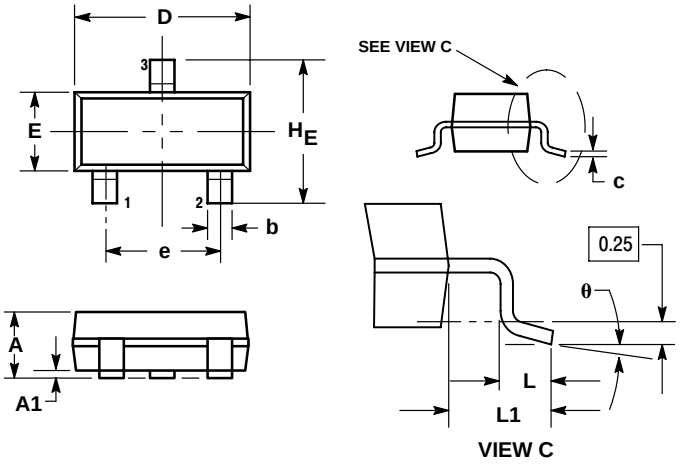


Figure 10. Diode Forward Voltage vs. Current

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−08
ISSUE AN

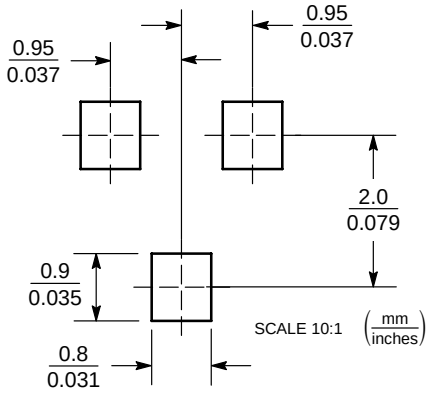


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318−01 THRU −07 AND −09 OBSOLETE, NEW STANDARD 318−08.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H_E	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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